

T610H

High temperature 6 A sensitive TRIACs

Features

- Medium current TRIAC
- Logic level sensitive TRIAC
- 150 °C max. T_i turn-off commutation
- Clip bounding
- RoHS (2002/95/EC) compliant package

Applications

- The T610H is designed for the control of AC actuators in appliances and industrial systems.
- The multi-port drive of the microcontroller can control the multiple loads of such appliances and systems through this sensitive gate TRIAC.

Description

Specifically designed to operate at 150 °C, the new 6 A T610H TRIAC provides an enhanced performance in terms of power loss and thermal dissipation. This allows the optimization of the heatsink size, leading to space and cost effectiveness when compared to electromechanical solutions.

Based on ST logic level technology, the T610H offers an I_{GT} lower than 10 mA and specified minimal commutation and high noise immunity levels valid up to the T_i max.

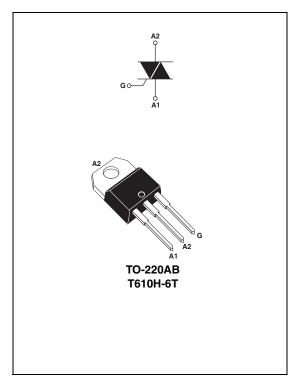


Table 1. Device summary

Symbol	Value	Unit	
I _{T(RMS)}	6	Α	
V _{DRM} /V _{RRM}	600	V	
I _{GT MAX}	10	mA	

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Table 2. Absolute maximum ratings

Symbol	Parameter			Value	Unit	
I _{T(RMS)}	On-state rms current (full sine wave) $T_c = 138 ^{\circ}\text{C}$		6	Α		
1	Non repetitive surge peak on-state	F = 60 Hz	t = 16.7 ms	63	Α	
ITSM	current (full cycle, T _j initial = 25 °C)	F = 50 Hz	t = 20 ms	20 ms 60		
l ² t	I ² t Value for fusing	t _p = 10 ms		24	A ² s	
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 120 Hz	T _j = 150 °C	50	A/μs	
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage	t _p = 10 ms	T _j = 25 °C	V _{DRM} /V _{RRM} + 100	V	
I _{GM}	Peak gate current $t_p = 20 \mu s$ $T_j = 150 ^{\circ} C$		4	Α		
P _{G(AV)}	Average gate power dissipation $T_j = 150 ^{\circ}\text{C}$		1	W		
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 150	°C	

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Symbol	Test conditions Quadrant		Min.	Max.	Unit
I _{GT}	V _D = 12 V R _I = 33 Ω	1 - 11 - 111	1	10	mA
V _{GT}	AD - 15 A LIF - 22 75	1 - 11 - 111		1.0	V
V_{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$	1 - 11 - 111	0.15		V
I _H ⁽¹⁾	I _T = 100 mA			25	mA
I_L $I_G = 1.2 I_{GT}$	1.121	I - III		30	A
	IG = 1.2 IGT	II		35	- mA
dV/dt (1)	V _D = 67% V _{DRM,} gate open, T _j = 150 °C	75		V/µs	
(dl/dt)c (1) Logic level, 0.1 V/ μ s, T _j = 150 °C			8.7		A/ms
(ui/ut)c · /	Logic level, 15 V/ μ s, T _j = 150 °C		2.3		Allis

^{1.} For both polarities of A2 referenced to A1.

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Table 4. Static characteristics

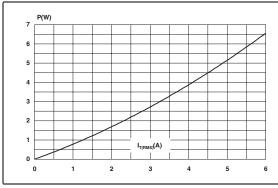
Symbol	Test cond	Value	Unit		
V _T ⁽¹⁾	$I_{TM} = 8.5 \text{ A}, t_p = 380 \ \mu \text{s}$	T _j = 25 °C	MAX.	1.5	٧
V _{t0} (1)	Threshold voltage	T _j = 150 °C	MAX.	0.8	٧
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	MAX.	62	mΩ
	V _{DRM} = V _{RRM}	T _j = 25 °C	MAX.	5	μΑ
I _{DRM}		T _j = 150 °C	MAX.	2.7	
I _{RRM}	V _D /V _R = 400 V (at peak mains voltage)	T _j = 150 °C	MAX.	2.2	mA
	V _D /V _R = 200 V (at peak mains voltage)	T _j = 150 °C	MAX.	1.8	

^{1.} for both polarities of A2 referenced to A1.

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	1.8	°C/W
R _{th(j-a)}	Junction to ambient	60	C/VV

Figure 1. Maximum power dissipation versus Figure 2. On-state rms current versus case on-state rms current (full cycle) temperature (full cycle)



T_(PAMS)(A)

7

6

5

4

3

2

1

T_c(°C)

0

25

50

75

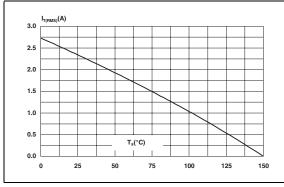
100

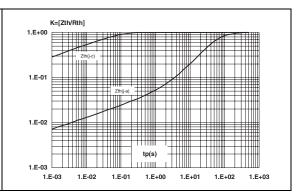
125

150

Figure 3. On-state rms current versus ambient temperature (free air convection, full cycle)

Figure 4. Relative variation of thermal impedance, versus pulse duration





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Figure 5. Relative variation of gate trigger current and voltage versus junction temperature (typical values)

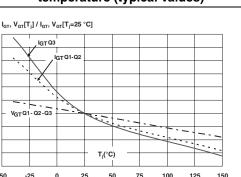


Figure 6. Relative variation of holding and latching current versus junction temperature (typical values)

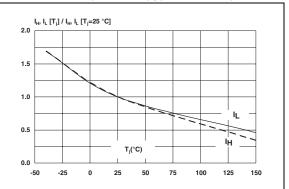
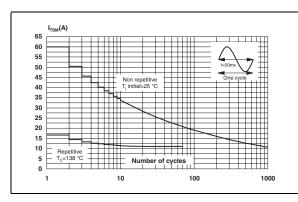


Figure 7. Surge peak on-state current versus number of cycles

1.5

1.0

Figure 8. Non-repetitive surge peak on-state current and corresponding value of I²t



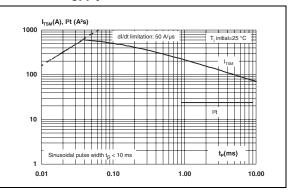
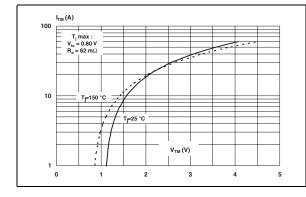
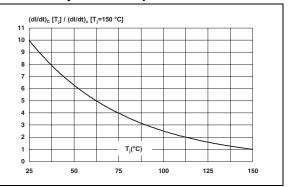


Figure 9. On-state characteristics (maximum values)

Figure 10. Relative variation of critical rate of decrease of main current versus junction temperature



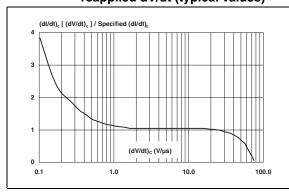


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decrease of main current versus reapplied dV/dt (typical values)

Relative variation of critical rate of Figure 12. Relative variation of static dV/dt immunity versus junction temperature



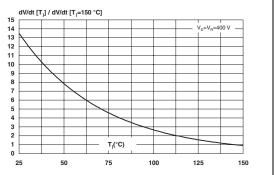
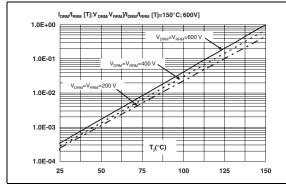
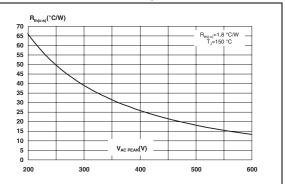


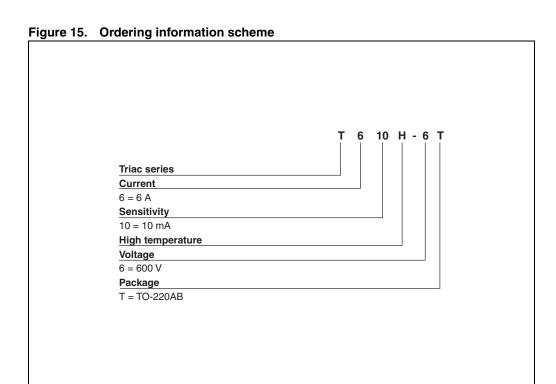
Figure 13. Variation of leakage current versus Figure 14. Acceptable case to ambient thermal junction temperature for different values of blocking voltage

resistance versus repetitive peak off-state voltage





2 Ordering information scheme



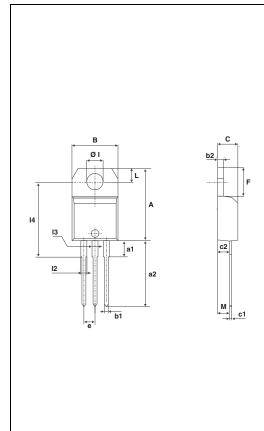
T610H Package information

3 Package information

- Epoxy meets UL94, V0
- Recommended torque 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-220AB dimensions



	Dimensions					
Ref.	Millimeters		Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
В	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
С	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
е	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
ØI	3.75		3.85	0.147		0.151
14	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
12	1.14		1.70	0.044		0.066
13	1.14		1.70	0.044		0.066
М		2.60			0.102	

Ordering information T610H

4 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T610H-6T	T610H 6T	TO-220AB	2.3 g	50	Tube

5 Revision history

Table 8. Document revision history

Date	Revision	Changes
15-May-2009	1	First issue.

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